TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

# GT5G131

#### Strobe Flash Applications

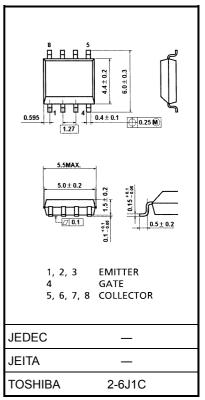
Unit: mm

- 3-V gate drive voltage: V<sub>GE</sub> = 3.0 V (min) (@I<sub>C</sub> = 130 A)
- Supplied in compact and thin package requires only a small mounting area
- 5th generation (trench gate structure) IGBT
- Enhancement-mode
- Peak collector current: IC = 130 A (max)

#### Maximum Ratings (Ta = 25°C)

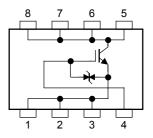
| Characteristics                      |       | Symbol           | Rating  | Unit |  |
|--------------------------------------|-------|------------------|---------|------|--|
| Collector-emitter voltage            |       | $V_{CES}$        | 400     | V    |  |
| Gate-emitter voltage                 | DC    | $V_{GES}$        | ±6      | V    |  |
|                                      | Pulse | $V_{GES}$        | ±8      |      |  |
| Collector current                    | DC    | IC               | 5       | A    |  |
|                                      | 1 ms  | I <sub>CP</sub>  | 130     |      |  |
| Collector power dissipation (Note 1) |       | P <sub>C</sub>   | 1.1     | W    |  |
| Junction temperature                 |       | Tj               | 150     | °C   |  |
| Storage temperature range            |       | T <sub>stg</sub> | -55~150 | °C   |  |

Note 1: Drive operation: Mount on glass epoxy board [1 inch $^2 \times$  1.5 t]



Weight: 0.080 g (typ.)

#### **Equivalent Circuit**



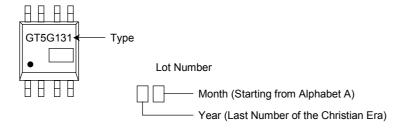
These devices are MOS type. Users should follow proper ESD handling procedures. Operating condition of turn-off dv/dt should be lower than 400 V/ $\mu$ s.

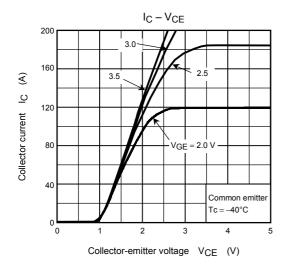
## Electrical Characteristics (Ta = 25°C)

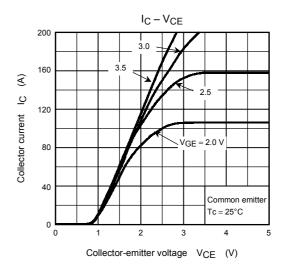
| Chara                    | acteristics        | Symbol                | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------|--------------------|-----------------------|--|-----|------|-----|------|
| Gate leakage cur         | rent               | I <sub>GES</sub>      | $V_{GE} = \pm 6 \text{ V}, V_{CE} = 0$   | _   | _    | ±10 | μΑ   |
| Collector cut-off of     | current            | I <sub>CES</sub>      | V <sub>CE</sub> = 400 V, V <sub>GE</sub> = 0   | _   | _    | 10  | μΑ   |
| Gate-emitter cut-        | off voltage        | V <sub>GE (OFF)</sub> | I <sub>C</sub> = 1 mA, V <sub>CE</sub> = 5 V   | 0.5 | _    | 1.0 | V    |
| Collector-emitter        | saturation voltage | V <sub>CE</sub> (sat) | I <sub>C</sub> = 130 A, V <sub>GE</sub> = 3 V  | _   | 2.2  | 7.0 | V    |
| Input capacitance        | )                  | C <sub>ies</sub>      | V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1 MHz   | _   | 2800 | _   | pF   |
| Switching time Fall time | Rise time          | t <sub>r</sub>        | $\begin{array}{c} 3 \text{ V} \\ 0 \\ \end{array}$ $\begin{array}{c} 30  \Omega \\ \text{O} \\ \end{array}$ $\begin{array}{c} \text{CI} \\ \text{SM} \\ \text{NIN: } t_r \leq 100 \text{ ns} \\ t_f \leq 100 \text{ ns} \\ \text{Duty cycle} \leq 1\% \end{array}$ $\begin{array}{c} 30  \Omega \\ \text{O} \\ $ |     | 1.3  |     | - μs |
|                          | Turn-on time       | t <sub>on</sub>       |  | _   | 1.4  | _   |      |
|                          | Fall time          | t <sub>f</sub>        |  |     | 1.5  |     |      |
|                          | Turn-off time      | t <sub>off</sub>      |  | _   | 1.8  | _   |      |
| Thermal resistant        | ce (Note 2)        | R <sub>th (j-a)</sub> | _  | _   |      | 114 | °C/W |

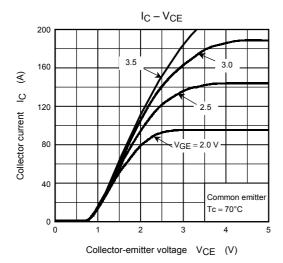
Note 2: Drive operation: Mount on glass epoxy board [1 inch $^2 \times$  1.5 t]

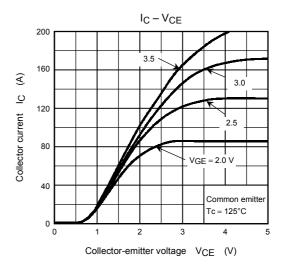
### Marking

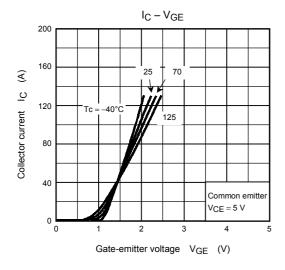


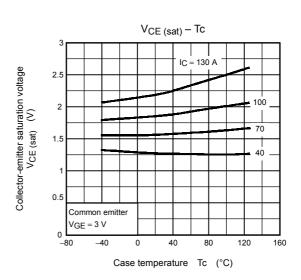


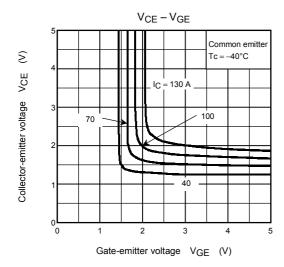


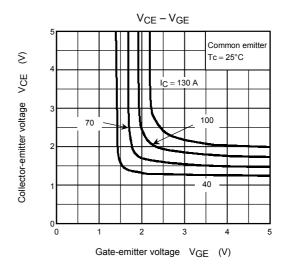


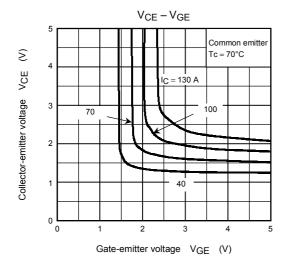


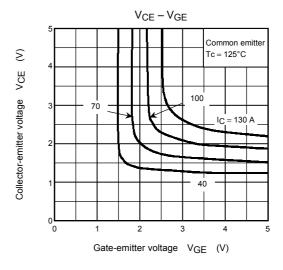


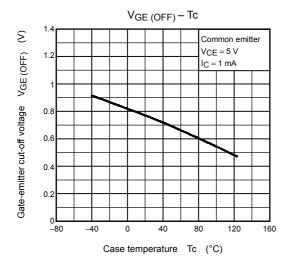


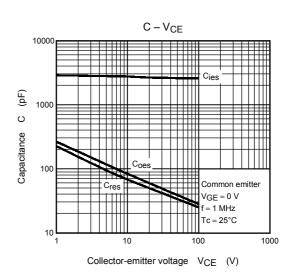




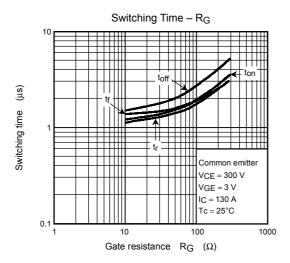


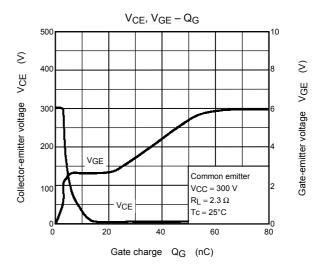


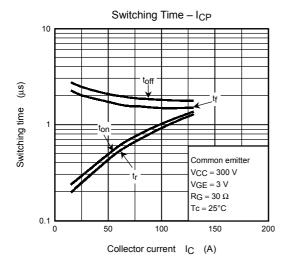


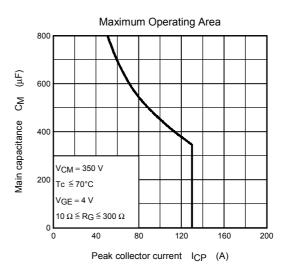


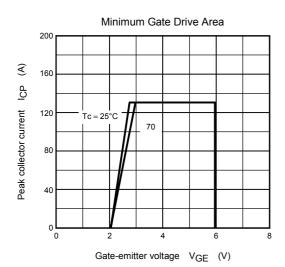
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